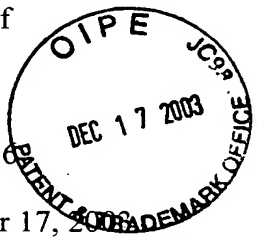
Docket No. PTGF-03057
HIR.076

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re patent application of

Naoki Shibata, et al.



Serial No.: 10/664,056 Group Art Unit: Not Yet Assigned

Filing Date: September 17, 2003 Examiner: Unknown

For: III GROUP NITRIDE SYSTEM COMPOUND SEMICONDUCTOR LIGHT EMITTING ELEMENT

Honorable Commissioner of Patents
Alexandria, Virginia 22313-1450

INFORMATION DISCLOSURE STATEMENT

Sir:

Under the provisions of 37 CFR §1.97 through §1.99 and pursuant to applicant's duty of disclosure under 37 CFR §1.56, applicant respectfully brings the following documents listed on the attached form PTO-1449, to the attention of the Examiner in charge of the above-identified application. Copies of the listed documents are provided herewith for the convenience of the Examiner.

In compliance with the concise explanation requirement under 37 CFR §1.98(a)(3), the relevance of these documents is discussed on pages 1 and 2 of the subject application. Further, an English-language Abstract is attached to one of the references.

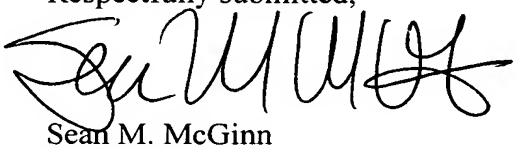
Additionally, as a concise statement of relevance for Hirayama, et al., this reference discloses a light emitting device that includes: a light emitting layer of $In_{0.05}Al_{0.34}Ga_{0.61}N$ (80 nm thick); and a Si-doped n-AlGaN layer with Al content of 18% (600 nm thick) and a Mg doped p-AlGaN layer with Al content of 18% (600 nm) formed on n-and p-sides, respectively, of the light emitting layer (See Fig. 8). Namely, the Al content of the n-and p-AlGaN layers is less than that of the light emitting layer. However, even assuming aguendo that the magnitude relationship in the Al content between the n-or p-AlGaN layer and the light emitting layer is disclosed, the invention claimed in claims 1 to 8 relates to the Al content in a quantum well structure, whereas Hirayama, et al., does not describe, teach, or suggest any thing about the magnitude relationship in the Al content of a quantum well structure.

This citation does not constitute an admission that the references are relevant or material to the claims. They are only cited as constituting related art of which the applicant is aware.

It is respectfully requested that the listed references be considered by the Examiner and formally made of record in this application.

Please charge any deficiencies in fees and credit any overpayment of fees to Attorney's Deposit Account No. 50-0481.

Respectfully submitted,



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INFORMATION DISCLOSURE CITATION

(Use several sheets if necessary)

Docket Number (Optional)	Application Number
PTGF-03057	10/664,056
Applicant(s)	
Naoki Shibata, et al.	
Filing Date	**Group Art Unit**
September 17, 2003	Not Yet Assigned

U.S. PATENT DOCUMENTS

*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE

FOREIGN PATENT DOCUMENTS

	REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation YES	Translation NO
		2000-294884	10/20/2000	Japan			ABS	

OTHER DOCUMENTS *(Including Author, Title, Date, Pertinent Pages, Etc.)*

		Hideki Hirayama, et al., "300 nm band high intensity ultraviolet LED using four element mixed crystal InAlGaN", Monthly Display 2001 August Separate Volume, , August 2001.

EXAMINER	DATE CONSIDERED

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.